
MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

	SYMBOLS	1N 4001	1N 4002	1N	1N 4004				UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=75^{\circ}C$	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.1							Volts
Maximum DC reverse current $T_A=25^{\circ}C$ at rated DC blocking voltage $T_A=100^{\circ}C$	I_R	5.0 50.0							μA
Typical junction capacitance (NOTE 1)	C_J	15.0							pF
Typical thermal resistance (NOTE 2)	$R_{\theta JA}$	50.0							$^{\circ}C/W$
Operating junction and storage temperature range	T_J, T_{STG}	-65 to +175							$^{\circ}C$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted



1N4001 THRU 1N4007

GENERAL PURPOSE SILICON RECTIFIER

